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Kind regards,

Team Nexperia

NPN resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 47 k Ω

Rev. 7 — 21 December 2011

Product data sheet

1. Product profile

1.1 General description

NPN Resistor-Equipped Transistor (RET) family in small Surface-Mounted Device (SMD) plastic packages.

Table 1. Product overview

Type number	Package			PNP	Package	
	NXP	JEITA	JEDEC	complement	configuration	
PDTC123JE	SOT416	SC-75	-	PDTA123JE	ultra small	
PDTC123JM	SOT883	SC-101	-	PDTA123JM	leadless ultra small	
PDTC123JT	SOT23	-	TO-236AB	PDTA123JT	small	
PDTC123JU	SOT323	SC-70	-	PDTA123JU	very small	

1.2 Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design

1.3 Applications

- Digital application in automotive and industrial segments
- Control of IC inputs

- Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified
- Cost-saving alternative for BC847/857 series in digital applications
- Switching loads

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	50	V
I _O	output current		-	-	100	mA
R1	bias resistor 1 (input)		1.54	2.20	2.86	kΩ
R2/R1	bias resistor ratio		17	21	26	



NPN resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 47 k Ω

2. Pinning information

Pin	Description	Simplified outline	Graphic symbol
SOT23; S	OT323; SOT416		
1	input (base)	_	
2	GND (emitter)	3	
3	output (collector)	2	1 R1 R2 sym007
SOT883			
1	input (base)		
2	GND (emitter)		
3	output (collector)	2 Transparent top view	1 R1 R2 Sym007

3. Ordering information

Type number	Package	ckage					
	Name	Description	Version				
PDTC123JE	SC-75	plastic surface-mounted package; 3 leads	SOT416				
PDTC123JM	SC-101	leadless ultra small plastic package; 3 solder lands; body 1.0 \times 0.6 \times 0.5 mm	SOT883				
PDTC123JT	-	plastic surface-mounted package; 3 leads	SOT23				
PDTC123JU	SC-70	plastic surface-mounted package; 3 leads	SOT323				

4. Marking

Type number	Marking code ^[1]
PDTC123JE	28
PDTC123JM	DW
PDTC123JT	*25
PDTC123JU	*49

[1] * = placeholder for manufacturing site code.

PDTC123J_SER Product data sheet

2 of 17

NPN resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 47 k Ω

5. Limiting values

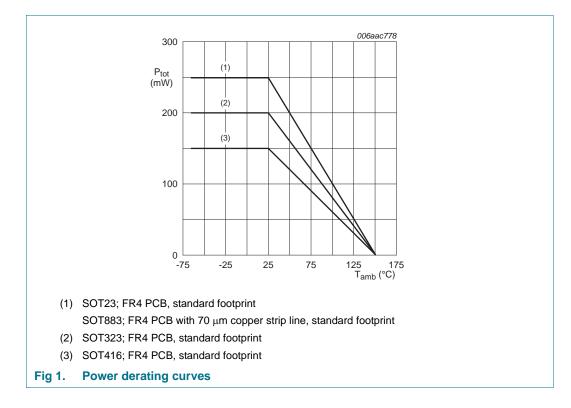
Table 6. In accorda	Limiting values ance with the Absolute Maxim	num Rating System (IEC 60	0134).			
Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	50	V
V _{CEO}	collector-emitter voltage	open base		-	50	V
V_{EBO}	emitter-base voltage	open collector		-	10	V
VI	input voltage					
	positive			-	+12	V
	negative			-	-5	V
lo	output current			-	100	mA
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$		-	100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$				
	PDTC123JE (SOT416)		[1][2]	-	150	mW
	PDTC123JM (SOT883)		[2][3]	-	250	mW
	PDTC123JT (SOT23)		<u>[1]</u>	-	250	mW
	PDTC123JU (SOT323)		<u>[1]</u>	-	200	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	+150	°C
T _{stg}	storage temperature			-65	+150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

[3] Device mounted on an FR4 PCB with 70 µm copper strip line, standard footprint.

NPN resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 47 k Ω



6. Thermal characteristics

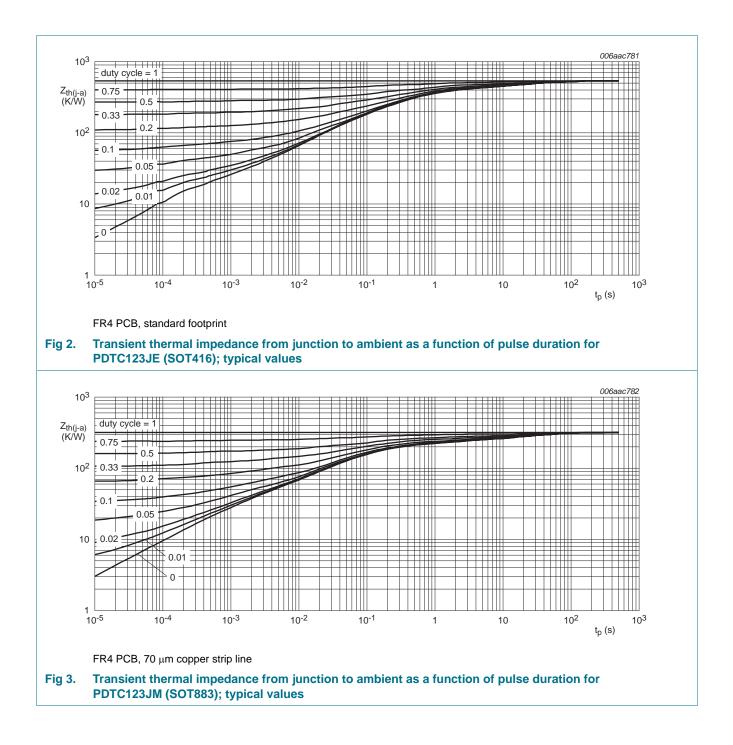
Table 7.	Thermal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air					
	PDTC123JE (SOT416)		[1][2]	-	-	830	K/W
	PDTC123JM (SOT883)		[2][3]	-	-	500	K/W
	PDTC123JT (SOT23)		<u>[1]</u>	-	-	500	K/W
	PDTC123JU (SOT323)		<u>[1]</u> .	-	-	625	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

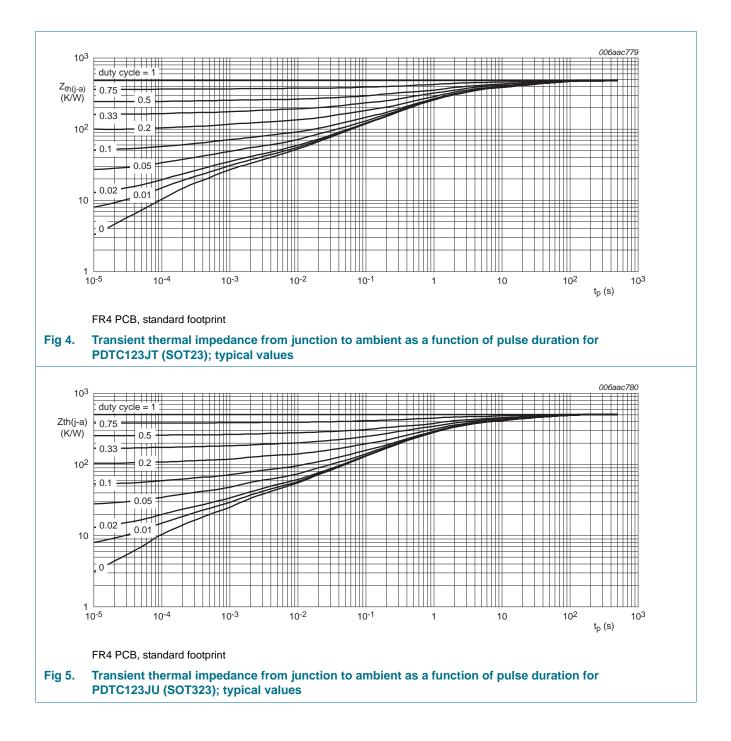
[2] Reflow soldering is the only recommended soldering method.

[3] Device mounted on an FR4 PCB with 70 μ m copper strip line, standard footprint.

PDTC123J series



PDTC123J series



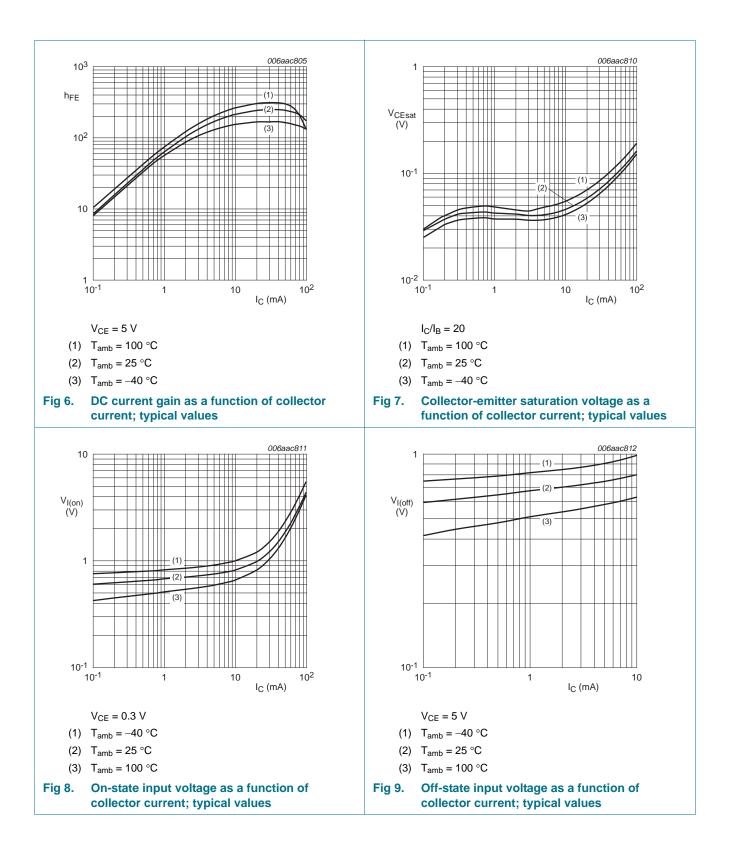
NPN resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 47 k Ω

7. Characteristics

Table 8. $T_{amb} = 25$	Characteristics °C unless otherwise sp	ecified.				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off current	$V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}$	-	-	100	nA
I _{CEO}	collector-emitter	$V_{CE} = 30 \text{ V}; I_B = 0 \text{ A}$	-	-	1	μΑ
	cut-off current	V _{CE} = 30 V; I _B = 0 A; T _j = 150 °C	-	-	5	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 V; I_{C} = 0 A$	-	-	180	μΑ
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 10 \text{ mA}$	100	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_{C} = 5 \text{ mA}; I_{B} = 0.25 \text{ mA}$	-	-	100	mV
V _{I(off)}	off-state input voltage	$V_{CE} = 5 \text{ V}; \text{ I}_{C} = 100 \mu\text{A}$	-	0.6	0.5	V
V _{I(on)}	on-state input voltage	V_{CE} = 0.3 V; I _C = 5 mA	1.1	0.75	-	V
R1	bias resistor 1 (input)		1.54	2.20	2.86	kΩ
R2/R1	bias resistor ratio		17	21	26	
C _c	collector capacitance	$\label{eq:VCB} \begin{array}{l} V_{CB} = 10 \text{ V}; \text{I}_{\text{E}} = \text{i}_{\text{e}} = 0 \text{ A}; \\ \text{f} = 1 \text{ MHz} \end{array}$	-	-	2.5	pF
f _T	transition frequency	$V_{CE} = 5 \text{ V}; I_{C} = 10 \text{ mA};$ f = 100 MHz	<u>[1]</u> -	230	-	MHz

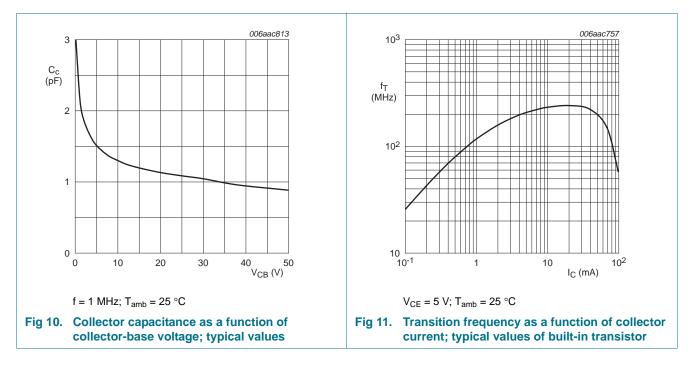
[1] Characteristics of built-in transistor.

PDTC123J series



PDTC123J series

NPN resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 47 k Ω



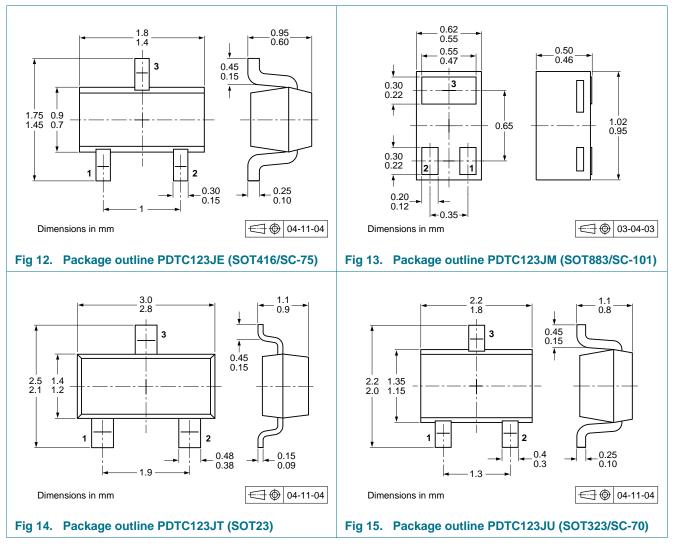
8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

NPN resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 47 k Ω

9. Package outline



10. Packing information

Table 9. Packing methods

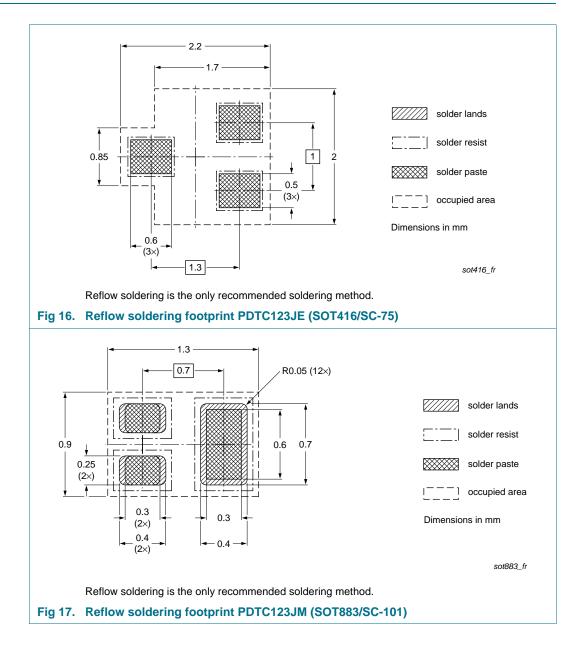
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

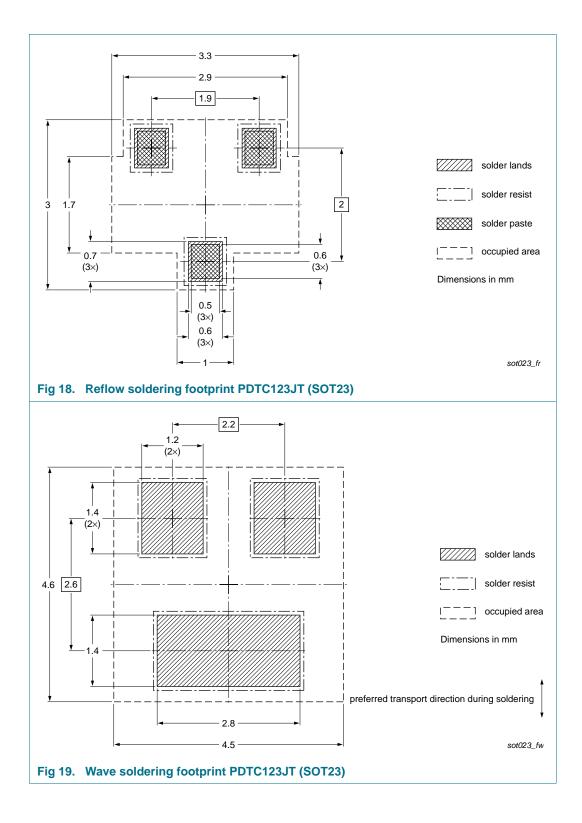
Type number	Package	Description	Packing	Packing quantity		
			3000	10000		
PDTC123JE	SOT416	4 mm pitch, 8 mm tape and reel	-115	-135		
PDTC123JM	SOT883	2 mm pitch, 8 mm tape and reel	-	-315		
PDTC123JT	SOT23	4 mm pitch, 8 mm tape and reel	-215	-235		
PDTC123JU	SOT323	4 mm pitch, 8 mm tape and reel	-115	-135		

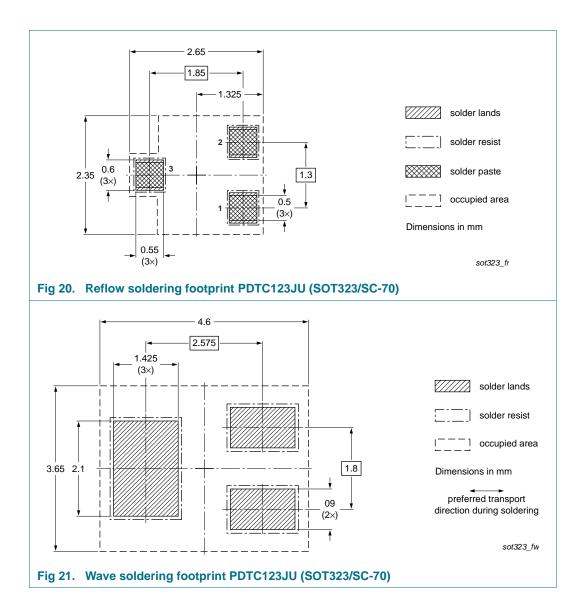
[1] For further information and the availability of packing methods, see Section 14.

NPN resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 47 k Ω

11. Soldering







NPN resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 47 k Ω

12. Revision history

Table 10. Revision histo	ry			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PDTC123J_SER v.7	20111221	Product data sheet	-	PDTC123J_SER v.6
Modifications:	 Figure 3 and 	d <u>5</u> : corrected		
PDTC123J_SER v.6	20111215	Product data sheet	-	PDTC123J_SERIES v.5
PDTC123J_SERIES v.5	20040813	Product data sheet	-	PDTC123J_SERIES v.4
PDTC123J_SERIES v.4	20030410	Product specification	-	-

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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PDTC123J_SER

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NPN resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 47 k Ω

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PDTC123J series

NPN resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 47 k Ω

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